

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
MAGRI' ET AL.)

Serial No. **NOT YET ASSIGNED**)

Filing Date: **HEREWITH**)

For: **VERTICAL-CONDUCTION AND**)
PLANAR-STRUCTURE MOS DEVICE)
WITH A DOUBLE THICKNESS OF)
GATE OXIDE AND METHOD)
REALIZING POWER VERTICAL)
MOS TRANSISTORS WITH)
IMPROVED STATIC AND DYNAMIC)
PERFORMANCES AND HIGH)
SCALING DOWN DENSITY)

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PRELIMINARY AMENDMENT

MS Patent Application
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Prior to the calculation of fees and examination of
the present application, please enter the amendments and
remarks set out below.